

	<p>SI4114DY-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI4114DY-T1-GE3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET N-CH 20V 20A 8-SOIC</p> <p>Datenblätter:  SI4114DY-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 79999 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI4114DY-T1-GE3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET N-CH 20V 20A 8-SOIC
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	79999 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	8-SOIC (0.154", 3.90mm Width)
Supplier Device-Gehäuse	8-SO
Verlustleistung (max)	2.5W (Ta), 5.7W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	20A (Tc)
Rds On (Max) @ Id, Vgs	6 mOhm @ 10A, 10V
VGS (th) (Max) @ Id	2.1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	95nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	3700pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±16V
Verpackung	Tape & Reel (TR)



















































SI4114DY-T1-GE3 ist neu im Original, Suche SI4114DY-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI4114DY-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI4114DY-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI4114G-BM Energy Micro (Silicon Labs) IC RF FREQ SYNTH VCO 28QFN</p>	 <p>SI4114DY-T1-E3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 20A 8-SOIC</p>	 <p>SI4114DY-T1 VISHAY VISHAY SO-8</p>	 <p>SI4114GM-EVB Energy Micro (Silicon Labs) BOARD EVAL SI4114G-BM</p>
 <p>SI4114G-BMR SILICON SILICON CLCC</p>	 <p>SI4114DY-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 20A 8-SOIC</p>	 <p>SI4114G-B-GM Energy Micro (Silicon Labs) IC RF SYNTH FOR GSM/GPRS 28QFN</p>	 <p>SI4115G-BM Energy Micro (Silicon Labs) FREQUENCY GSM/GPRS SYNTH EXT</p>

heiße Teile

Mehr

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|---|---|---|---|---|
|  SI4058DY |  SI4090DY |  SI4100BDDY-T1-GE3 |  SI4100DY |  SI4100DY-T1-E3 |
|  SI4100DY-T1-E3 |  SI4100DY-T1-GE3 |  SI4100DY-T1-GE3 |  SI4102DY |  SI4102DY-T1-E3 |
|  SI4102DY-T1-E3 |  SI4102DY-T1-GE3 |  SI4102DY-T1-GE3 |  SI4104DY-T1-GE3 |  SI4104DY-T1-GE3 |
|  SI4108DY-T1-GE3 |  SI4108DY-T1-GE3 |  SI4110DY-T1-GE3 |  SI4110DY-T1-GE3 |  SI4112-D-GM |
|  SI4113-BMR |  SI4114DY |  SI4114DY-T1-E3 |  SI4114DY-T1-E3 |  SI4114DY-T1-GE3 |
|  SI4116DY |  SI4116DY-T1-E3 |  SI4116DY-T1-E3 |  SI4116DY-T1-GE3 |  SI4116DY-T1-GE3 |
|  SI4122-BTR |  SI4122-D-GMR |  SI4122DY-T1-E3 |  SI4122G-BMR |  SI4123-BM |
|  SI4124DY-T1-E3 |  SI4124DY-T1-E3 |  SI4124DY-T1-GE3 |  SI4124DY-T1-GE3 |  SI4126-BMR |
|  SI4126DY-T1-E3 |  SI4128BDY |  SI4128BDY-T1-GE3 |  SI4128DY-T1-GE3 |  SI4128DY |
|  SI4128DY-T1 |  SI4128DY-T1-E3 |  SI4128DY-T1-E3 |  SI4128DY-T1-GE3 |  SI4128DY-T1-GE3 |

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